





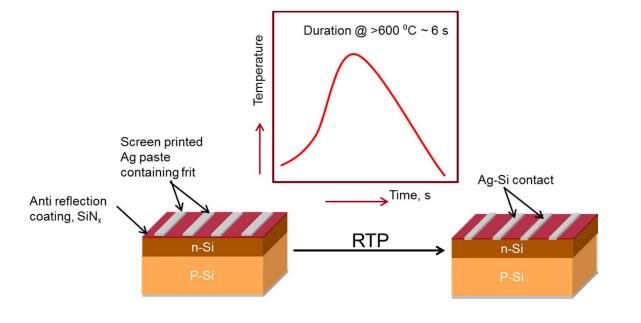




In situ rapid thermal processing / X-ray diffraction for materials forensics

Introduction

- Rapid thermal processing (RTP) : Widely used for processing materials in the photovoltaic (PV) industry, most notably for metal contact formation in Si solar cells
- Ag-Si contact processing time : ~10 seconds
- RTP parameters have evolved empirically over time
 - Lack of in-situ time resolved characterization facility with time resolution <1 sec.
- Several alternative mechanisms/reaction pathways proposed mainly based on ex-situ studies
- Precise mechanism/ reaction pathways uncertain



Contact processing

- Screen printing silver paste over anti-reflection coating
- Firing @ ~ 750-800 °C
- Ramp rates > 50 °C/s

Proposed Mechanisms

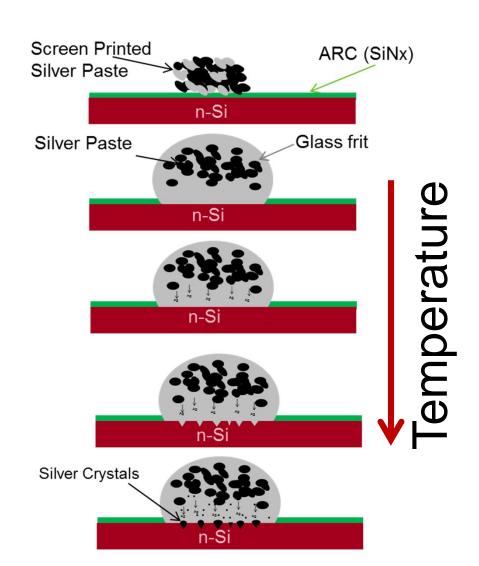
SiNx etching

1. PbO based Frit: SiO₂, PbO, B₂O₃, ZnO, NiO SiNx+2PbO \longrightarrow SiO₂ +2Pb+ x/2N₂ (1) 2. Silver can dissolve in glass frit

SiNx+2Ag₂O \rightarrow SiO₂ +4Ag+ x/2N₂ (2)

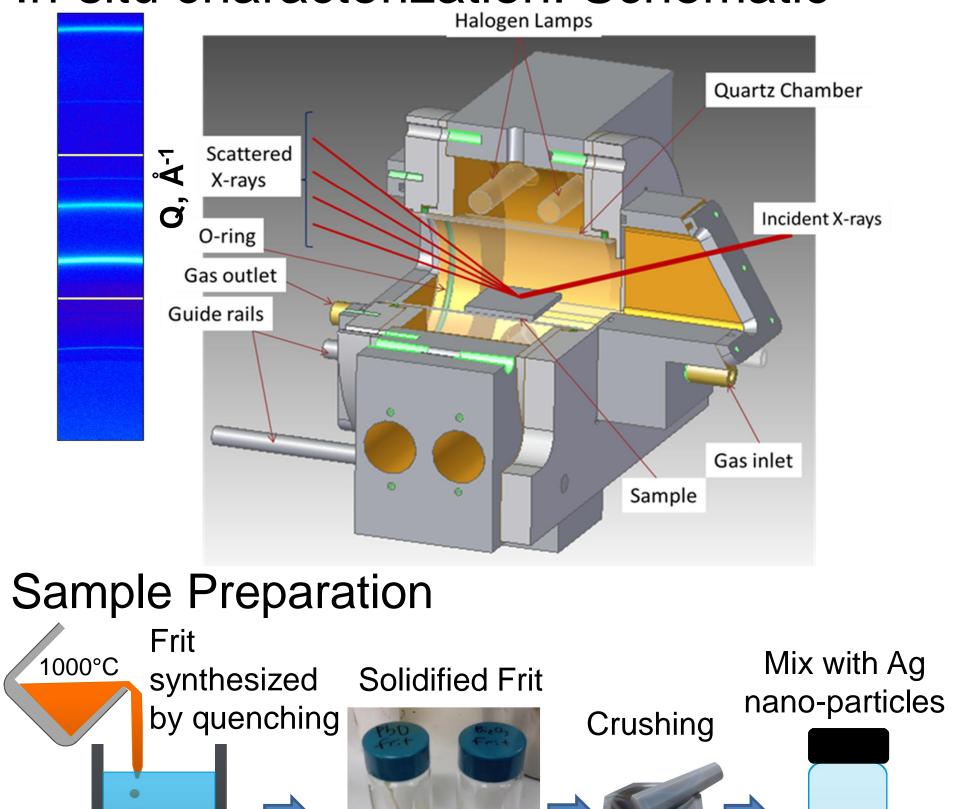
Ag deposition

1. Ag dissolved in glass can deoxidize at the Si surface: 2Ag₂O+Si $4Ag + SiO_2$ (3) 2. Ag forms ternary liquid alloys with Pb and Si which separate out on cooling



RTP Setup

In-situ characterization: Schematic

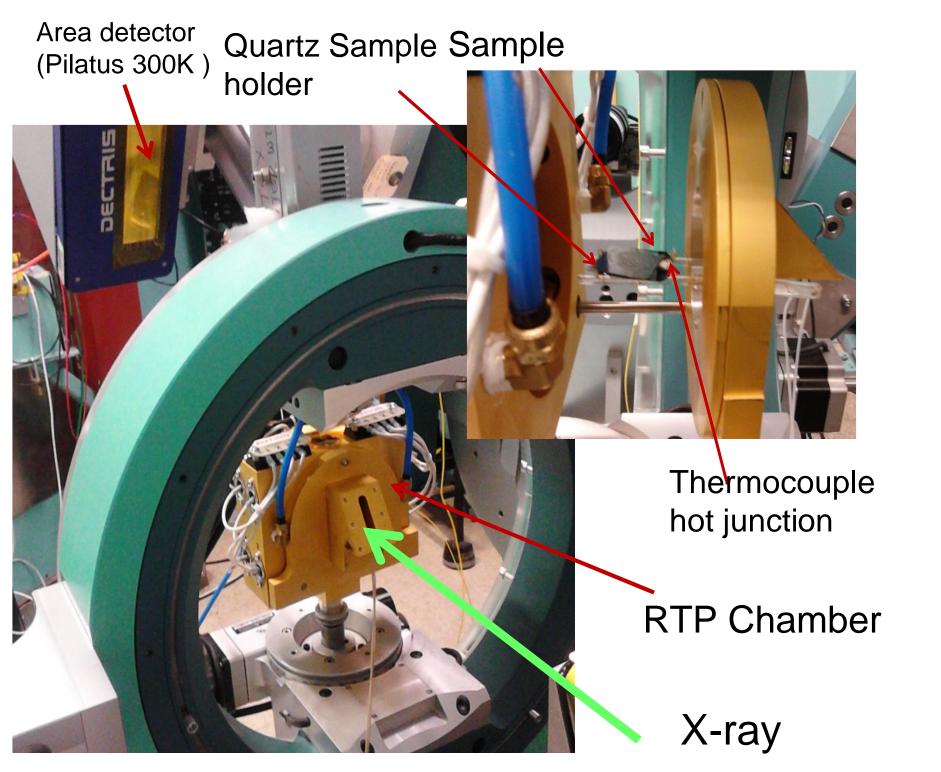


• PbO frit mixed with all combinations of Si, SiNx, Ag nanoparticles

Equal parts by mole ratio in all combinations

Ahmad, Van Campen, Fields, Yu, Pool, Parilla, Ginley, Van Hest, Toney. "Rapid thermal processing chamber for insitu x-ray diffraction." *Review of Scientific Instruments* 86, no. 1 (2015): 013902.

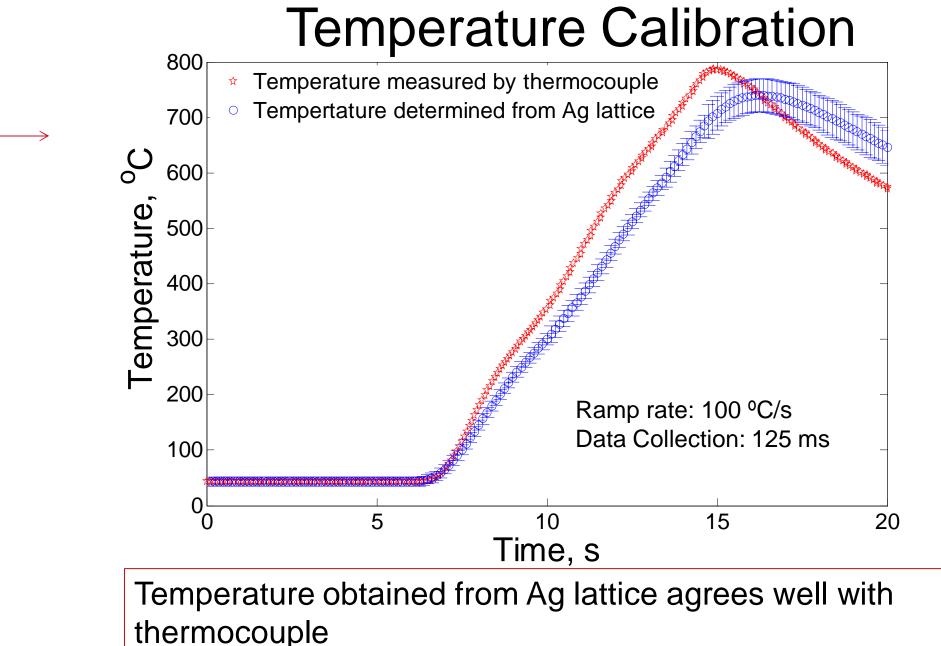
RTP Setup in Beamline 7-2 @ SSRL



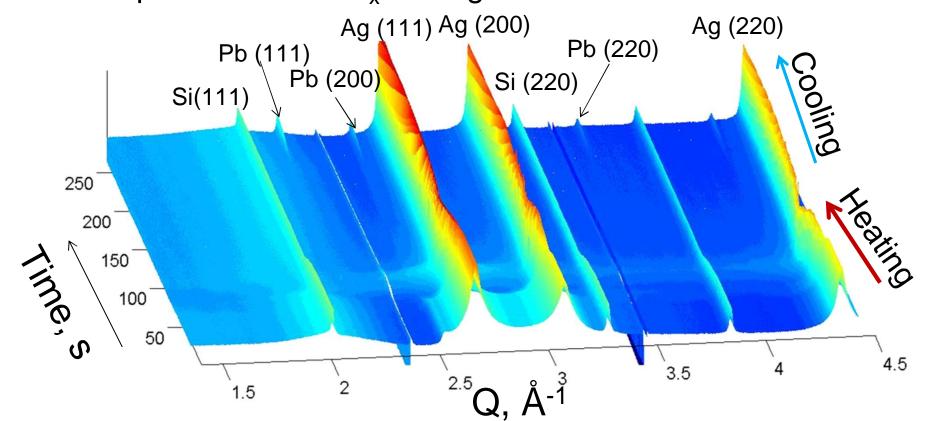
Frit Composition

Frit	Active Component	Glass Network	Components
	PbO	SiO ₂	B_2O_3
1	mol %	mol %	mol %
	60	30	10

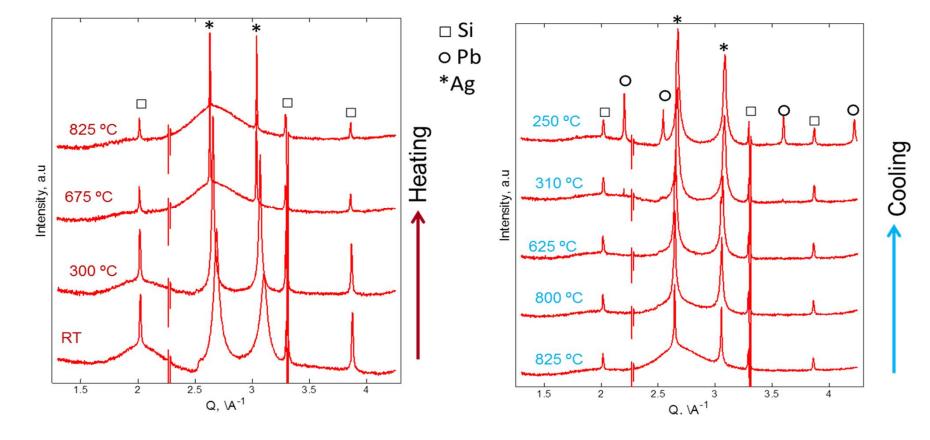
Ag-Si cell contact formation mechanism



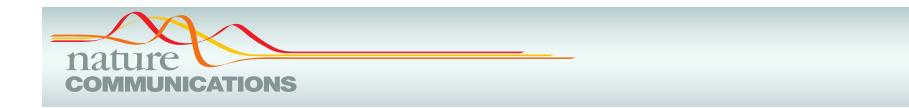
Sample:PbO-frit+SiN_x+Si+Ag



Processed in Air: Heating rate 100 °C/s PbO-frit+Si+SiN_x+Ag powder mixture (1:1:1:1)

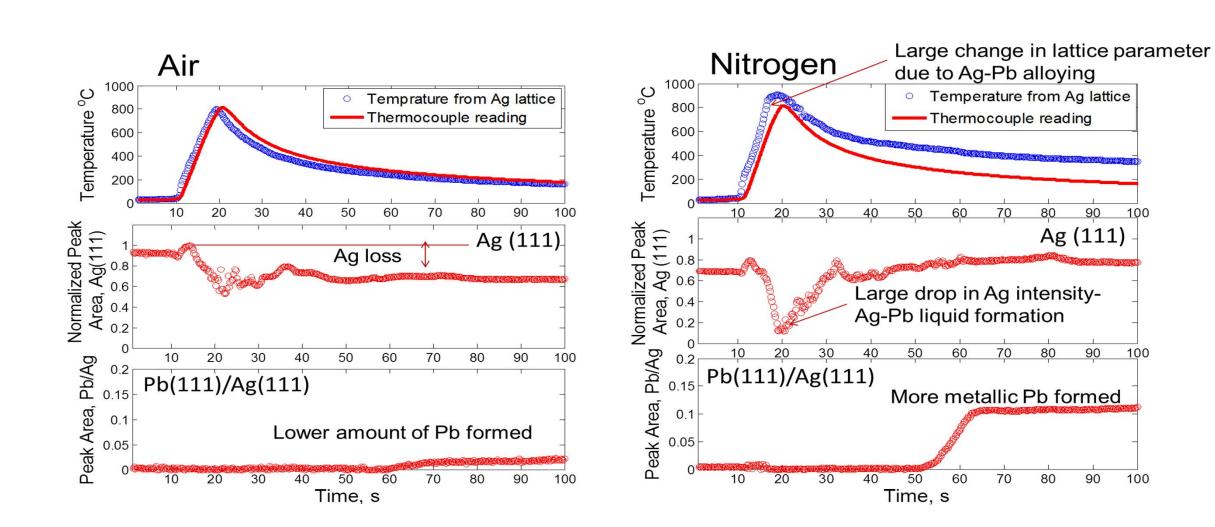


- Grain growth of Ag on heating
- Appearance of diffused scattered peak below Ag(111): Ag-Pb liquid formation
- Ag(111) peak intensity increases on cooling with slight broadening (due to Ag nano-crystal formation).



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Effect of Processing environment: Air Vs Nitrogen



- Ag loss in Air : Ag dissolution in frit followed by precipitation of tiny particles on cooling
- Ag deposition on Si surface and etching should be coupled for contact formation: Ag⁺ dissolved in frit attacks the Si surface and Ag is deposited according to reaction.

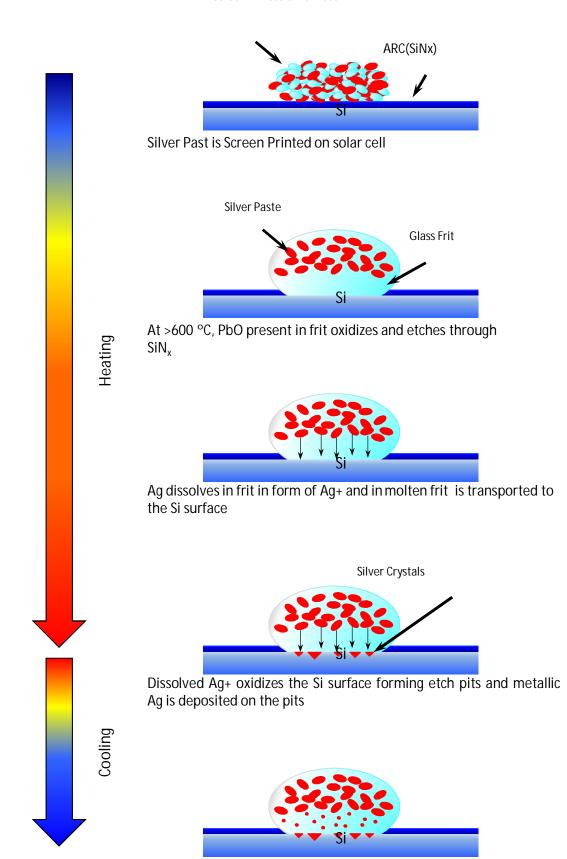
Key Observations

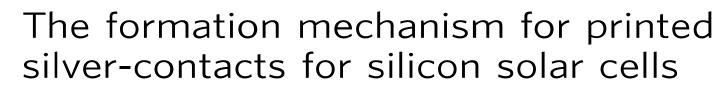
- More metallic Pb upon processing in nitrogen atmosphere -reaction (1)
- Grater reduction in Ag peak intensity upon firing in nitrogen : More Ag-Pb liquid formation
- Ag loss upon processing in Air : Ag dissolution in frit followed by precipitation on cooling to form very small particles.
- Ag deposition on Si surface and etching of Si should be coupled for contact formation: Ag dissolved in frit can preferentially attacks Si surface and get deposited – reaction (3)

Summary

SiN_x Etching $SiN_x + 2PbO \rightarrow SiO_2 + 2Pb + (x/2)N_2$ (1) Or $SiN_x + 2Ag_2O \rightarrow SiO_2 + 4Ag + (x/2)N_2$ (2)

Ag deposition: $2Ag + (1/2)O \rightarrow Ag_2O$ (3) then $2Ag_2O + Si \rightarrow SiO_2 + 4Ag$ (4)

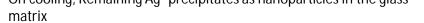




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Si does not form ternary liquid with Pb and Ag. Binary Ag-Pb liquid observed.



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